

San PRODI	Jose, CA 96138	'HANGE NOTIC'	E (PCN)		
PCN #: W1510-01 DATE: March 14, 2016 Product Affected: 280G-50LF(T), 280G-57LF(T), 290GI- 34LF(T)		MEANS OF DISTINGUISHING CHANGED DEVICES: Product Mark Back Mark Date Code Prefix Z5 before datecode Other			
Date Effective: June 14, 2016					
Contact: IDT PCN DESK		Attachment: Yes	No No		
E-mail: pcndesk@idt.com		Samples: Available upon	request		
DESCRIPTION AND PURPOSE OF C	CHANGE:				
 Die Technology Wafer Fabrication Process Assembly Process Equipment Material Testing Manufacturing Site Data Sheet 	This notification is to advis production site from United Manufacturing Corporation The UMC wafer technolog process. This process has b the parts on this PCN. There is no expected chang	e our customers that IDT has a Microelectronics Corporation (TSMC). v is a .35um process and will b een previously qualified by ID e to the data sheet, package or	made a change to the wafer fabrication (UMC) to Taiwan Semiconductor be manufactured on a TSMC .35um T and with the same fab base used for backend manufacturing process.		
□ Data Sheet	There is no change in order the top mark.	ring part number. The change will be indicated by a die step change on			
	Please see attachments for	ualification data.			
RELIABILITY/QUALIFICATION SU Based on wafer and component level quareliability of the product.	J MMARY: alification and characterizati	on tests, there is no change to	the performance or		
CUSTOMER ACKNOWLEDGMENT IDT records indicate that you require wr to grant approval or request additional in it will be assumed that this change is acc IDT reserves the right to ship either vers on the earlier version has been depleted.	COF RECEIPT: itten notification of this chan formation. If IDT does not a ceptable. ion manufactured after the p	nge. Please use the acknowled eceive acknowledgement with rocess change effective date u	gement below or E-Mail in 30 days of this notice ntil the inventory		
Customer:	[] Approval for shipments	prior to effective date.		
Name/Date:	E	-Mail Address:			
Title:	F	hone# /Fax# :			
CUSTOMER COMMENTS:					
IDT ACKNOWLEDGMENT OF REC	CEIPT:				
RECD. BY:		DATE:			



Integrated Device Technology, Inc. 6024 Silver Creek Valley Road San Jose, CA 96138

PRODUCT/PROCESS CHANGE NOTICE (PCN)

ATTACHMENT I - PCN # : W1510-01

PCN Type: Wafer Fab Manufacturing Site Change - UMC to TSMC

Data Sheet Change: No

Detail Of Change:

This notification is to advise our customers that IDT has made a change to the wafer fabrication production site from United Microelectronics Corporation (UMC) to Taiwan Semiconductor Manufacturing Corporation (TSMC). The UMC wafer technology is a .35um process and will be manufactured on a TSMC .35um process. This process has been previously qualified by IDT and with the same fab base used for the parts on this PCN.

There is no expected change to the data sheet, package or backend manufacturing process.

There is no change in ordering part number. The change will be indicated by a die step change on the top mark.

Please contact your local IDT sales representative to request samples or additional information.



Product: 280G-50LF

Foundry: TSMC

Technology Information: CMOS 0.35 μ m

Report Date: Oct 15, 2015

Device Qual Test Results Summary

Test Description	Conditions	Sample Size	Rejects	Comments
ESD: Human Body Model	IDT Spec	3	0	2000V
ESD: Charged Device Model	JESD22-C101	3	0	750V
Latch-Up	JESD78	6	0	
Electrical Characterization	Per Datasheet	10*	-	

Note: * Sample size applies to base characterization



Product: 280G-57LF

Foundry: TSMC

Technology Information: CMOS 0.35 μ m

Report Date: Oct 15, 2015

Device Qual Test Results Summary

Test Description	Conditions	Sample Size	Rejects	Comments
ESD: Human Body Model	IDT Spec	3	0	2000V
ESD: Charged Device Model	JESD22-C101	3	0	750V
Latch-Up	JESD78	6	0	
Electrical Characterization	Per Datasheet	10*	-	

Note: * Sample size applies to base characterization



Product: 290GI-34LF

Foundry: TSMC

Technology Information: CMOS 0.35 µm

Report Date: Oct 15, 2015

Device Qual Test Results Summary

Test Description	Conditions	Sample Size	Rejects	Comments
ESD: Human Body Model	IDT Spec	3	0	2000V
ESD: Charged Device Model	JESD22-C101	3	0	750V
Latch-Up	JESD78	6	0	
Electrical Characterization	Per Datasheet	10*	-	

Note: * Sample size applies to base characterization



Foundry: TSMC

Technology Information: CMOS 0.35 μ m

Qualification Test Result Summary – JESD47 Recommended Tests

Test /Conditions	Conditions	Sample Size	Rejects	Comments
High Temperature Operating Life (Dynamic)	JESD22-A108D, +125°C, Vccmax @ 1000 hours or equivalent	77 77 77	0 0 0	
Temperature Cycle	JESD22-A104D, -55°C to +125°C, 700 cycles	25 25 25	0 0 0	
High Temperature Storage Bake	JESD22-A-103D, 150°C, 1000 hrs	25 25 25	0 0 0	
Highly Accelerated Stress Test (HAST)	EIA/JESD22-A110D, 130°C/85%R.H. Vcc max for 100 hours.	25 25 25	0 0 0	
Ball Shear Test	JESD22-B116A, Ball Shear Strength	5	0	

Note: For HAST and Temperature Cycle, samples have been subjected to pre-conditioning per JESD22-A113